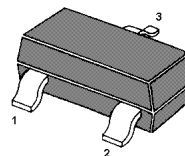
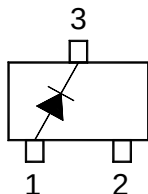


1SS294

SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

Features

- Small surface mounting type
- Low reverse current
- Low forward voltage



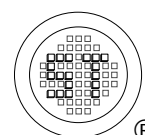
Marking Code: "XM"
TO-236 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	V_{RM}	45	V
Reverse Voltage	V_R	40	V
Average Forward Current	I_O	100	mA
Maximum Peak Forward Current	I_{FM}	300	mA
Power Dissipation	P_D	150	mW
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 125	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 100\text{ mA}$	V_F	0.6	V
Reverse Current at $V_R = 40\text{ V}$	I_R	5	μA
Total Capacitance at $V_R = 0\text{ V}$, $f = 1\text{ MHz}$	C_T	25	pF



Dated : 30/01/2007

